

REQUEST FOR ACCESS OF ABANDONED APPLICATION UNDER 37 CFR 1.14(a)

PROCESSED BY

JUN 25 1998

FIII

In re Application of

Harari Et. Al.

Application Number

337566

Filed

4/13/89

Group Art Unit

Examiner

Paper No. #31Assistant Commissioner for Patents
Washington, DC 20231

I hereby request access under 37 CFR 1.14(a)(3)(iv) to the application file record of the above-identified ABANDONED application, which is: (CHECK ONE)

- ☒ (A) referred to in United States Patent Number 5418752, column 1.
- ☐ (B) referred to in an application that is open to public inspection as set forth in 37 CFR 1.11, i.e., Application No. _____, filed _____, on page _____ of paper number _____.
- ☐ (C) an application that claims the benefit of the filing date of an application that is open to public inspection, i.e., Application No. _____, filed _____, or
- ☐ (D) an application in which the applicant has filed an authorization to lay open the complete application to the public.

Please direct any correspondence concerning this request to the following address:

Larry J. Hecker
Signature

6/25/98
Date

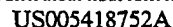
Larry J. Hecker
Typed or printed name

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Approved by: F. T. V.

(initials)

Unit: _____



[11] Patent Number: 5,418,752

[45] **Date of Patent:** **May 23, 1995**

- system design", *Computer Design*, Mar. 1, 1989, pp. 30 and 32.

- Primary Examiner**—Joseph A. Popek
Attorney, Agent, or Firm—Majestic, Parsons, Siebert & Hsue

- [57]
- ABSTRACT**

- A system of Flash EEPROM memory chips with controlling circuits serves as non-volatile memory such as that provided by magnetic disk drives. Improvements include selective multiple sector erase, in which any combinations of Flash sectors may be erased together. Selective sectors among the selected combination may also be de-selected during the erase operation. Another improvement is the ability to remap and replace defective cells with substitute cells. The remapping is performed automatically as soon as a defective cell is detected. When the number of defects in a Flash sector becomes large, the whole sector is remapped. Yet another improvement is the use of a write cache to reduce the number of writes to the Flash EEPROM memory, thereby minimizing the stress to the device from undergoing too many write/erase cycling.

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4 Claims, 5 Drawing Sheets

